



## > IDEAL STORAGE SOLUTION FOR NOTEBOOKS OR OTHER MOBILE DEVICES

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# CEA-Leti claims ultra-low variability in FDSOI devices at 22-nm

Semiconductor News

Anne-Francoise Pele
EE Times Europe
01/08/2009 1:29 PM



PARIS — CEA-Leti applied research center in microelectronics claimed it has achieved a record for device matching characteristics with an AVt of about 1mV.µm, below those obtained in bulk silicon technologies, while still maintaining Ion and Ioff characteristics.

The threshold voltage variation of less than 40mV across wafer, CEA-Leti specified, is also reported for 25-nm gate length Fully Depleted SOI (FDSOI) devices using undoped channel and high-k and metal gates technology.

According to CEA-Leti, the results show that the undoped channel FDSOI device with high-k/metal gate stack is a valid alternative to reduce variability issues at 22-nm and below.

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CEA-Leti said it has worked closely with STMicroelectronics NV (Geneva, Switzerland) and Soitec SA (Bernin, France) within the framework of the Medea+Decisif (Device and circuit performance boosted through silicon material fabrication) project.

The Decisif project aims to integrate performance

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Airbus uses Everspin's MRAMs
Everspin, the magnetoresistive
random access memory spin-off
from Freescale, has announced a
design win with Airbus for
advanced wide body aircraft.



ATIC offers to buy Chartered

ATIC has offered to buy Singaporean foundry Chartered Semiconductor and plans to fold it into its GlobalFoundries subsidiary.



### It's OLED on the phone

Global shipments of OLED displays for use in mobile phones are expected to rise by a factor of eight from 2009 to 2015, according to market trackers at iSuppli.



Blu-ray, Sony push 3D TV
The Blu-ray Disc Association is firming up plans to incorporate

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Strukturierte ASICs der

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3D TV content into the optical

http://www.eetimes.eu/semi/212701323

for low power and high performance applications, to lösen zunehmend FPGAs validate their impact by fabricating complex 45-nm node demonstrators directly comparable with bulk Si and to Nextreme Structured develop design kits and SOI-adapted circuit design for the **ASICs** evaluation by application designers. UML for C All White Papers »

boosters in fully and partially depleted SOI technologies



disc standard. Sony is also set to announce a major push into 3D. Smart metering Three industry associations have iointly devised a proposal for a manufacturer-independent

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